

GP15A - GP15M

AXIAL LEADED SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V

CURRENT: 1.5 A

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

- Case: DO-15
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.40 grams (approx.)
- Mounting Position: Any
- Marking: Type Number

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IX	HS	



DO-15							
Dim	Min	Max					
Α	25.40	_					
В	5.50	7.62					
С	0.686	0.889					
D	2.60	3.60					
All Dimensions in mm							

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbo	GP15A	GP15B	GP15D	GP15G	GP15J	GP15K	GP15M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	50	100	200	400	600	800	1000	v
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) $@T_A = 75^{\circ}C$	ю	1.5						A	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	50					A		
Forward Voltage $@I_F = 2.0A$	Vfm	1.1					V		
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	Iгм	5.0 200					μΑ		
Typical Junction Capacitance (Note 2)	Cj	15					pF		
Typical Thermal Resistance Junction to Ambient (Note 1)	R θ JA	45					°C /W		
Operating Temperature Range	Tj	-65 to +125					°C		
Storage Temperature Range	TSTG	-65 to +150				°C			

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.



RATING AND CHARACTERISTIC CURVES (GP15A - GP15M)





FIG.3 - TYPICAL FORWARD CHARACTERISTICS

FIG.4 - TYPICAL REVERSE CHARACTERISTICS

